

MJE15032 (NPN), MJE15033 (PNP)

Preferred Devices

Complementary Silicon Plastic Power Transistors

Designed for use as high-frequency drivers in audio amplifiers.

- DC Current Gain Specified to 5.0 Amperes
 $h_{FE} = 70$ (Min) @ $I_C = 0.5$ Adc
 $= 10$ (Min) @ $I_C = 2.0$ Adc
- Collector–Emitter Sustaining Voltage –
 $V_{CEO(sus)} = 250$ Vdc (Min) – MJE15032, MJE15033
- High Current Gain – Bandwidth Product
 $f_T = 30$ MHz (Min) @ $I_C = 500$ mAdc
- TO–220AB Compact Package
- Epoxy Meets UL94, V0 @ 1/8"
- ESD Ratings: Machine Model C
 Human Body Model 3B

MAXIMUM RATINGS

Rating	Symbol	MJE15032 MJE15033	Unit
Collector–Emitter Voltage	V_{CEO}	250	Vdc
Collector–Base Voltage	V_{CB}	250	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	8.0 16	Adc
Base Current	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	50 0.40	Watts W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0,016	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$

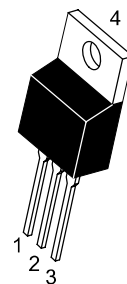


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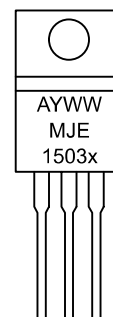
<http://onsemi.com>

**8.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY SILICON
250 VOLTS
50 WATTS**

MARKING DIAGRAM



TO–220
CASE 221A
STYLE 1



MJE1503x = Specific Device Code
 x = 2 or 3
 A = Assembly Location
 Y = Year
 WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MJE15032	TO–220	50 Units/Rail
MJE15033	TO–220	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.